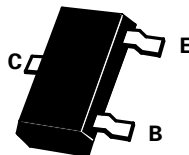


# SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - OCTOBER 1995

## FMMT597

COMPLEMENTARY TYPE FMMT497  
PARTMARKING DETAIL - 597



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-300	V
Collector-Emitter Voltage	$V_{CEO}$	-300	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-1	A
Continuous Collector Current	$I_C$	-0.2	A
Base Current	$I_B$	-200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	$I_C = -10mA^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu A$
Collector Cut-Off Current	$I_{CBO}$		-100	nA	$V_{CB} = -250V$
Emitter Cut-Off Current	$I_{EBO}$		-100	nA	$V_{EB} = -4V$
Collector-Emitter Cut-Off Current	$I_{CES}$		-100	nA	$V_{CES} = -250V$
Emitter Saturation Voltages	$V_{CE(sat)}$		-0.25 -0.25	V	$I_C = -50mA, I_B = -5mA$ $I_C = -100mA, I_B = -20mA^*$
	$V_{BE(sat)}$		-1.0	V	$I_C = -100mA, I_B = -20mA^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.85	V	$I_C = -100mA, V_{CE} = -10V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100	300		$I_C = -1mA, V_{CE} = -10V$ $I_C = -50mA, V_{CE} = -10V^*$ $I_C = -100mA, V_{CE} = -10V^*$
		100			
		100			
Transition Frequency	$f_T$	75		MHz	$I_C = -50mA, V_{CE} = -10V$ $f = 100MHz$
Output Capacitance	$C_{obo}$		10	pF	$V_{CB} = -10V, f = 1MHz$

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$

Spice parameter data is available upon request for this device

# FMMT597

## TYPICAL CHARACTERISTICS

